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Title: **JP2001189285A2: SELECTIVE HEATING METHOD OF SEMICONDUCTOR WAFER**

Country: JP Japan
Kind: A2 Document Laid open to Public Inspection

Inventor(s): **BILLIG MICHAEL STEVEN
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Applicant/Assignee: **LUCENT TECHNOLOG INC**
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Application Number: **JP20002000355111**

IPC Class: **H01L 21/28; H01L 21/26; H01L 21/314; H01L 21/3205;**

Priority Number(s): **Nov. 23, 1999 US19991999448349**

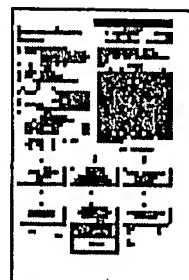
Abstract: **Problem to be solved:** To provide a manufacturing method of an integrated circuit for changing the rate of heat flow locally, by applying thin film made of each material for the sake of achieving different processing temperatures, particularly, when a wafer is heated at high temperatures, and changing material characteristics, such as emissivity, absorptivity, reflectivity, and so on.
Solution: A heating method includes a step for providing a wafer 30 having a surface 31, a step for changing a rate of heat flow at a part 32, by applying at least one layer of films 33 to at least one selective part 32 of the surface 31 and changing material characteristics, such as emissivity, absorptance, reflectivity and so on, a step for starting reaction at the part 32 by heating the wafer 30 at high temperatures, and a step for observing the temperatures of the wafer 30 and ending the heating under control of the heating, when a prescribed time has elapsed.

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Family: [Show known family members](#)

Other Abstract Info: none

Foreign References: No patents reference this one



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